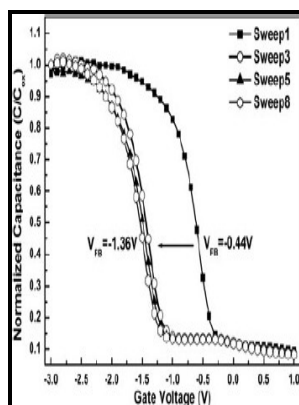


Characterization of Gd₂O₃ high-K dielectric films on Si(001)

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Characterization of Gd₂O₃

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Molecular beam epitaxy deposition of Gd₂O₃ thin films on SrTiO₃ (100) substrate

Zaumseil: Growth of crystalline praseodymium oxide on silicon. J-V characterization suggests Schottky and Poole-Frenkel are the dominant conduction in the deposited Gd₂O₃ films. Among numerous rare earth oxides, the gadolinium oxide Gd₂O₃ thin films have grown onto a wide range of substrates involving, e.

Characterization of gadolinium oxide film by pulse laser deposition

Temperature and flux from this cell can be adjusted more accurately than with conventional e-beam evaporators.

Characterization of gadolinium oxide film by pulse laser deposition

Czernohosky: TEM investigations of epitaxial high- k dielectrics on silicon. To be specially, there is about 7.

Molecular beam epitaxy deposition of Gd₂O₃ thin films on SrTiO₃ (100) substrate

During the growth, Gd₂O₃ powder 99. The obtained results indicated that the crystallinity of the films increased with increase in sputtering power and the films deposited at higher power showed the lower rms roughness value.

Characterization of gadolinium oxide film by pulse laser deposition

Pantelides: Bonding configurations and collective patterns of Ge atoms adsorbed on Si(111) - 7 × 7.

Growth of Crystalline Gd₂O₃ Thin Films with a High

Osten: Interface formation during molecular beam epitaxial growth of neodymium oxide on silicon. Thermodynamic stability of binary oxides in

contact with silicon.

Phase control of magnetron sputtering deposited Gd₂O₃ thin films as high

Although epitaxial layers of such ionic oxides with excellent structural quality can be grown using molecular beam epitaxy, they often exhibit poor electrical properties such as high leakage current density, flat band instability, poor reliability etc. Through the comparison between films grown at 450 and 570 °C, the existence of monoclinic phase caused an increase in J L by nearly one order of magnitude and a reduction of effective dielectric constant from 17 to 9.

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